

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Battery protection

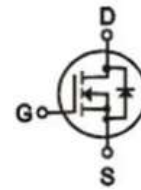
• Ordering Information:

Part NO.	ZMS015N08HP
Marking	ZMS015N08H
Packing Information	TUBE
Basic ordering unit (pcs)	1000

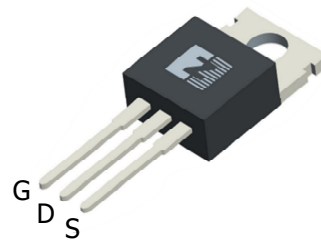
• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}	$25^\circ\text{C} \leq T_J \leq 175^\circ\text{C}$	80	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	140	A
	I_D	$T_C=75^\circ\text{C}$	140	A
	I_D	$T_C=100^\circ\text{C}$	129	A
Pulsed Drain Current ^①	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	420	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	167	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	5.0	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, VGS=10V, Rg=25 Ω ,	310	mJ
		L=0.5mH, VGS=10V, Rg=25 Ω ,	713	mJ
ESD Level (HBM)			CLASS 2	

• Product Summary



$V_{DS} = 80\text{V}$
 $R_{DS(ON)} = 1.8\text{m}\Omega$
 $I_D = 140\text{A}$



TO-220



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.9	°C/W
Thermal resistance, junction-ambient	$R_{thJA}^{②}$		-	30	°C/W
Soldering temperature	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0	2.7	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS} = 0V, V_{DS} = 80V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 30A$		1.8	2.4	m Ω
Forward Transconductance	g_{FS}	$V_{GS} = 5V, I_{SD} = 20A$		28		s
Diode Forward Voltage	V_{FSD}	$V_{GS} = 0V, I_{SD} = 30A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz, V_{DS} = 25V$	-	9130	-	pF
Output capacitance	C_{oss}		-	6640	-	
Reverse transfer capacitance	C_{rss}		-	117	-	
Gate Resistance	R_g	$f = 1MHz$	-	2.5		Ω
Total gate charge	Q_g	$V_{DD} = 15V, I_D = 20A, V_{GS} = 10V$	-	121	-	nC
Gate - Source charge	Q_{gs}		-	24	-	
Gate - Drain charge	Q_{gd}		-	23	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS} = 10V, V_{DS} = 15V, R_G = 3.3\Omega, I_D = 20A$	-	19	-	ns
Turn-ON Rise time	t_r		-	14	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	31	-	ns
Turn-Off Fall time	t_f		-	37	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD} = 20V, di_S/dt = 100A/s, I_S = 50A$	-	76	-	ns
Reverse Recovery Charge	Q_{RR}		-	120	-	nC

Fig.1 Gate-Charge Characteristics

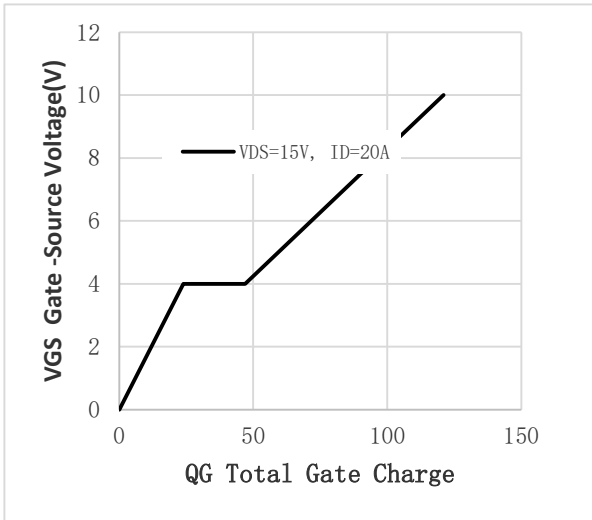


Fig.2 Capacitance Characteristics

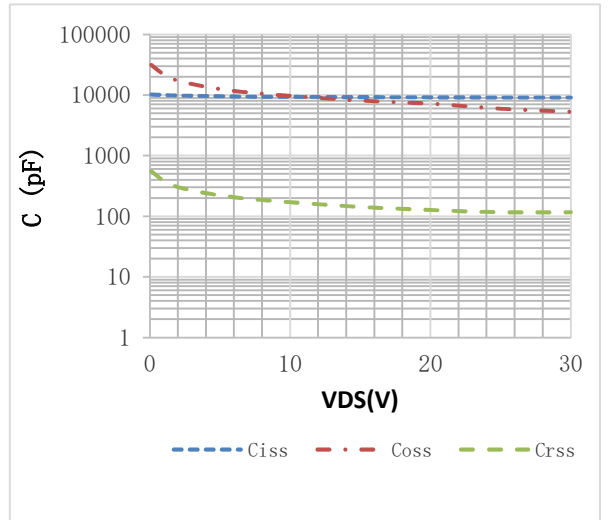


Fig.3 Power Dissipation

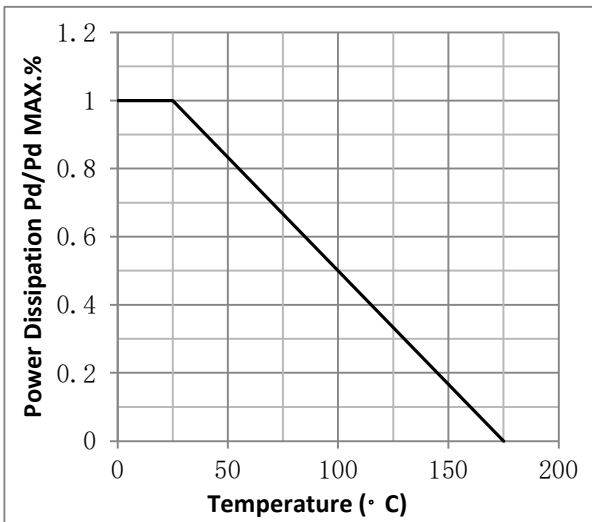


Fig.4 Typical output Characteristics

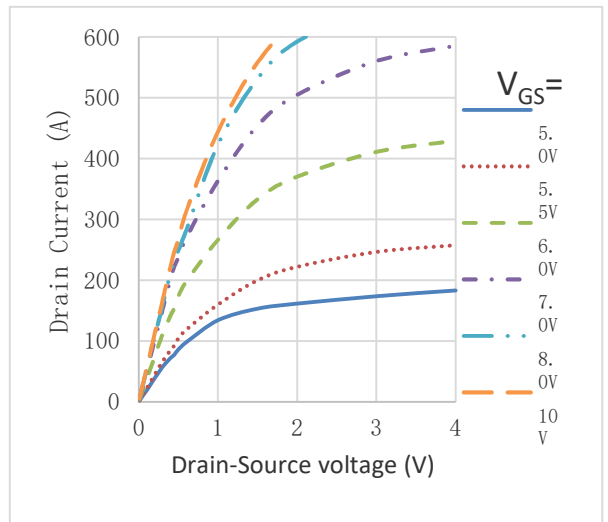


Fig.5 Threshold Voltage V.S Junction Temperature

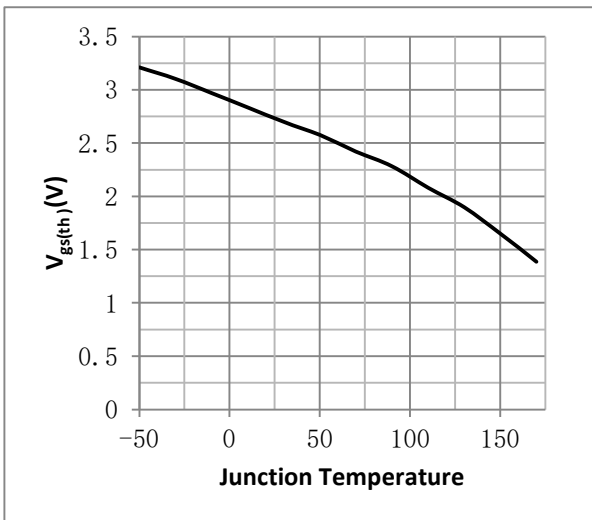


Fig.6 Resistance V.S Drain Current

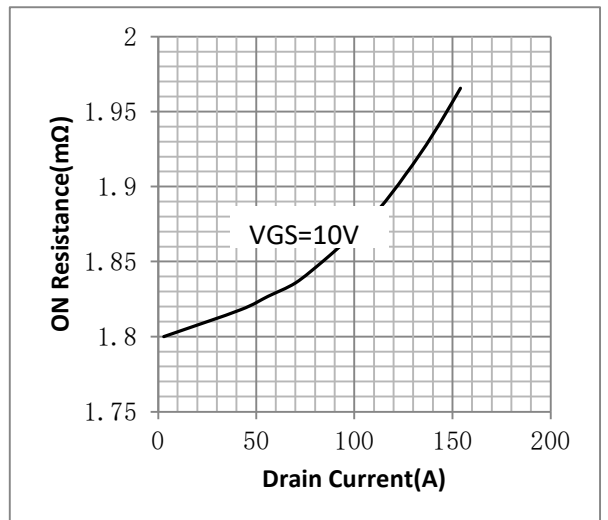


Fig.7 On-Resistance VS Gate Source Voltage

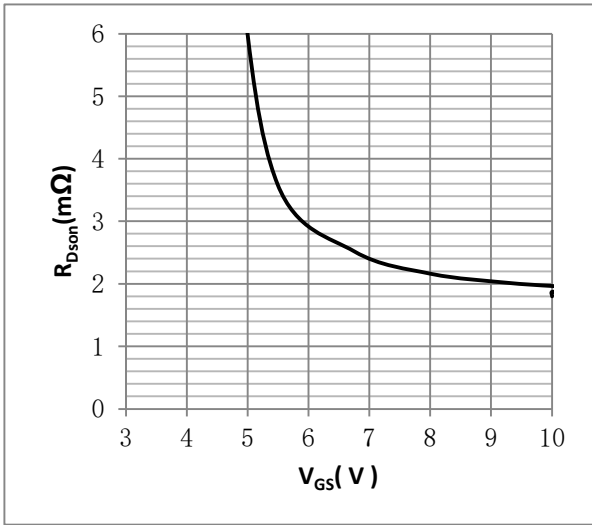


Fig.8 On-Resistance V.S Junction Temperature

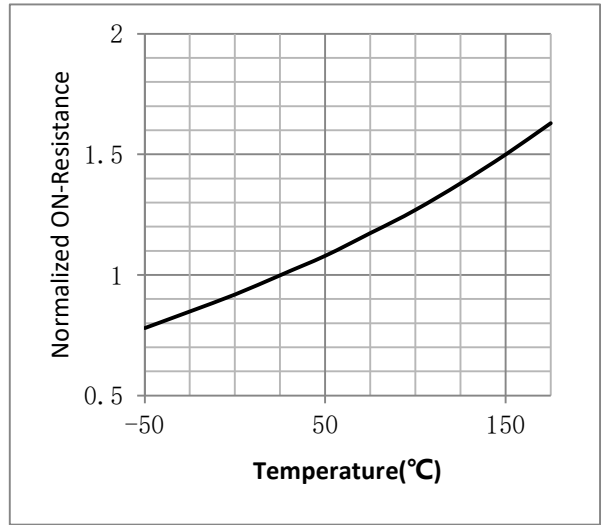


Figure 9. Diode Forward Voltage vs. Current

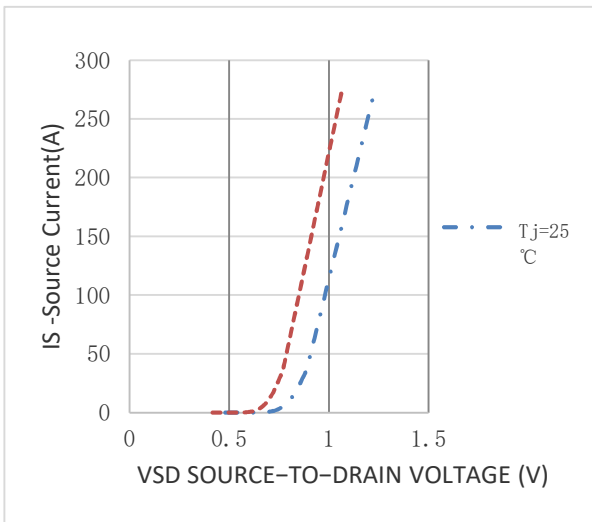


Figure 10. Transfer Characteristics

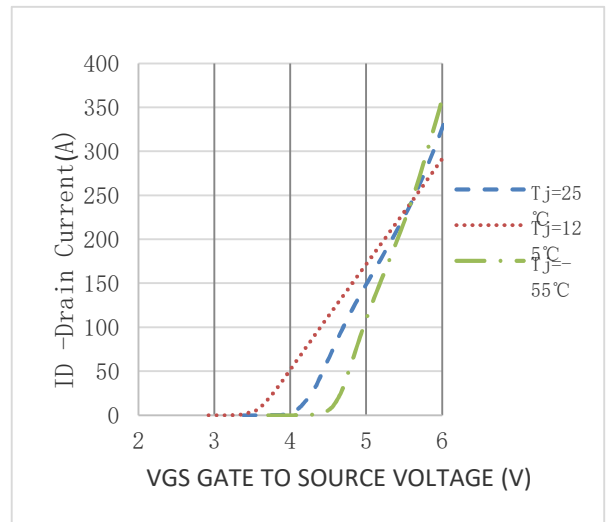


Fig.11 SOA Maximum Safe Operating Area

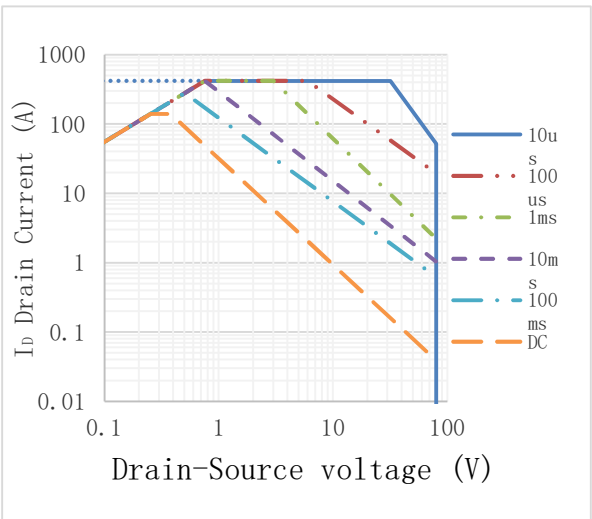
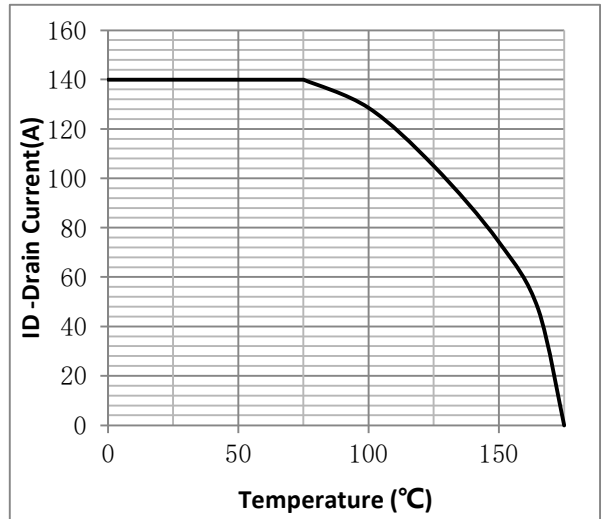
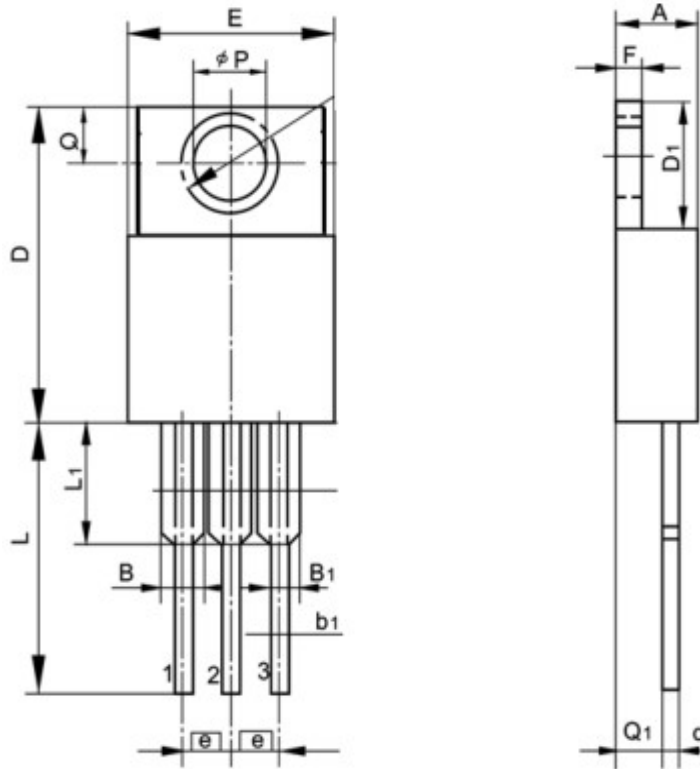


Fig.12 ID vs. Case Temperature^③



•TO-220 Package Outline

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	4.00		4.80	E	9.90		10.70
B	1.20		1.50	e		2.54	
B1	1.00		1.40	F	1.10		1.45
b1	0.65		1.00	L	12.50		14.50
c	0.35		0.75	L1	3.00	3.50	4.00
D	15.00		16.50	Q	2.50		3.00
D1	5.90		6.90	Q1	2.00		3.00



Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2021. 9. 6	
B	2022. 9. 5	1. Add Reach, HF figure, 2. ID modify
C	2024. 5. 20	Modify Qg curve.